

**650V/6A**

**SiC Schottky Barrier Diode**

**Characteristic**

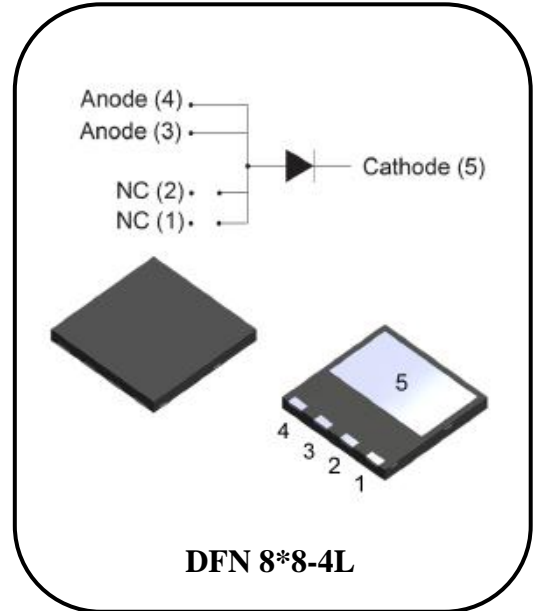
- Zero Reverse Recovery Current
- Positive temperature coefficient
- Temperature-independent performance
- High-speed switching
- Low switching loss
- Low heat dissipation requirements

**Application**

- Switching power supply
- Power factor correction
- Motor drive, traction
- Charging pile

**Product Description**

$V_{RRM}$	<b>650</b>	<b>V</b>
$I_F(135^\circ\text{C})$	<b>11</b>	<b>A</b>
$Q_C$	<b>17</b>	<b>nC</b>



Device	Package	Marking
<b>SDS065J006S3</b>	<b>DFN 8*8-4L</b>	<b>DS065006S3</b>

**Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit	Test Conditions
Reverse voltage (Repetitive peak)	$V_{RRM}$	650	V	$T_C=25^\circ\text{C}$
Reverse Voltage (Surge peak)	$V_{RSM}$	650		$T_C=25^\circ\text{C}$
Reverse voltage (DC)	$V_{DC}$	650		$T_C=25^\circ\text{C}$
Continuous forward current	$I_F$	23	A	$T_C=25^\circ\text{C}$
		11		$T_C=135^\circ\text{C}$
		6		$T_C=155^\circ\text{C}$
Surge non-repetitive forward current	$I_{FSM}$	48	A	$T_C=25^\circ\text{C}, t_p=10\text{ms}, \text{half Sine Pulse}$
Repetitive Peak Forward Surge Current	$I_{FRM}$	35	A	$T_C=25^\circ\text{C}, t_p=10\text{ms}, \text{half Sine Wave } D=0.1$
Total power dissipation	$P_{TOT}$	115	W	$T_C=25^\circ\text{C}$
$i^2t$ value	$\int i^2 dt$	11.5	$\text{A}^2\text{s}$	$T_C=25^\circ\text{C}, t_p=10\text{ms}$
Operating temperature	$T_j$	-55~175	$^\circ\text{C}$	
storage temperature	$T_{stg}$	-55~175	$^\circ\text{C}$	

### Thermal Characteristics

Parameter	Symbol	Values			Unit	Test Condition
		Min.	Typ.	Max.		
Thermal resistance	$R_{th(j-c)}$	/	1.3	/	$^{\circ}\text{C/W}$	

### Electrical Characteristics $T_J=25^{\circ}\text{C}$

Parameter	Symbol	Values			Unit	Test Condition
		Min.	Typ.	Max.		
DC blocking voltage	$V_{DC}$	650	/	/	V	$I_R=100\ \mu\text{A}$
Forward voltage	$V_F$	/	1.30	1.50	V	$I_F=6\text{A}, T_j=25^{\circ}\text{C}$
		/	1.55	1.80		$I_F=6\text{A}, T_j=175^{\circ}\text{C}$
Reverse current	$I_R$	/	1	18	$\mu\text{A}$	$V_R=650\text{V}, T_j=25^{\circ}\text{C}$
		/	2	48		$V_R=650\text{V}, T_j=175^{\circ}\text{C}$
Total capacitance	C	/	310	/	pF	$V_R=0\text{V}, f=1\text{MHz}$
		/	33	/		$V_R=200\text{V}, f=1\text{MHz}$
		/	28	/		$V_R=400\text{V}, f=1\text{MHz}$
Total capacitive charge	$Q_C$	/	17	/	nC	$V_R=400\text{V}$
Capacitance Stored Energy	$E_C$	/	2.6	/	$\mu\text{J}$	$V_R=400\text{V}$

### Typical Electrical Characteristics Curves

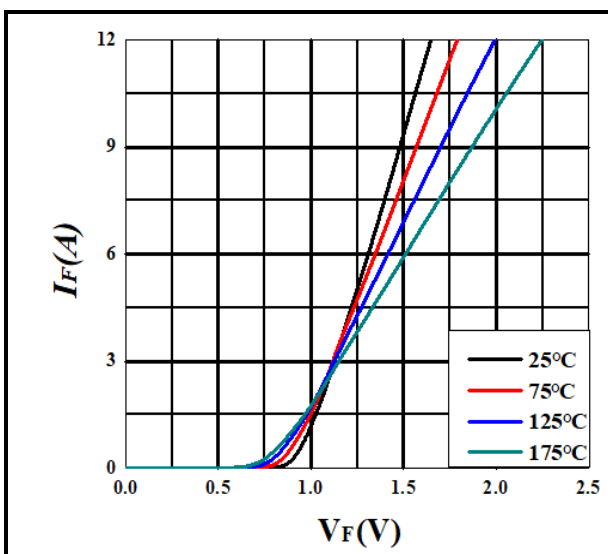


Figure 1. Forward Characteristics

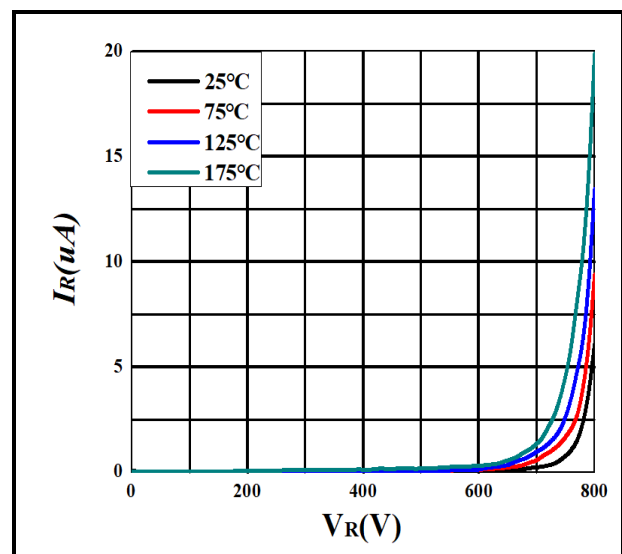


Figure 2. Reverse Characteristics

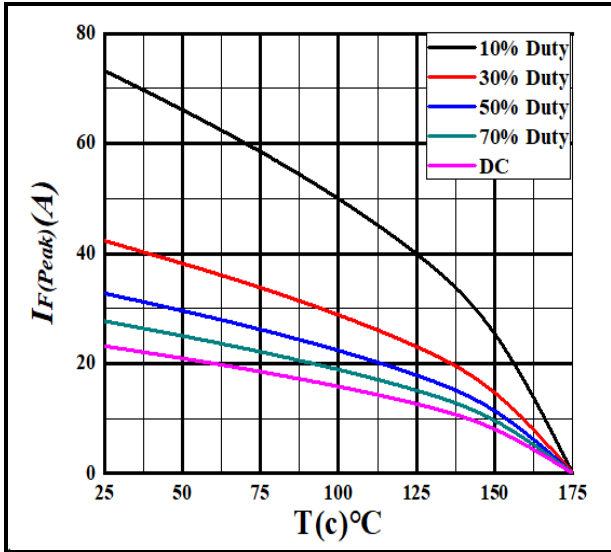


Figure 3. Current Derating

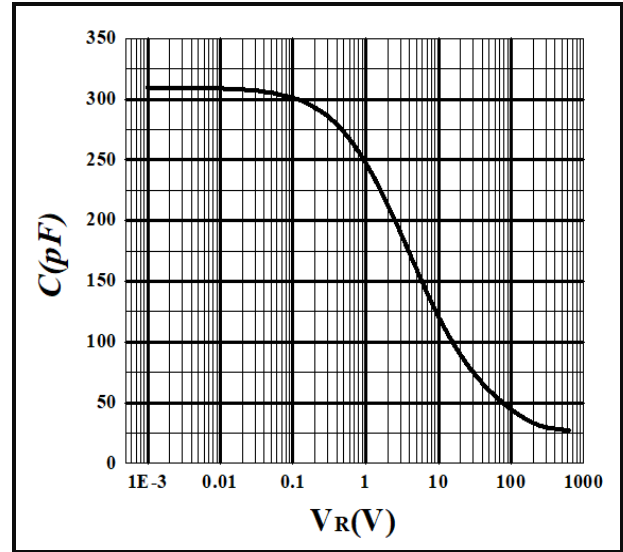


Figure 4. Capacitance vs. Reverse Voltage

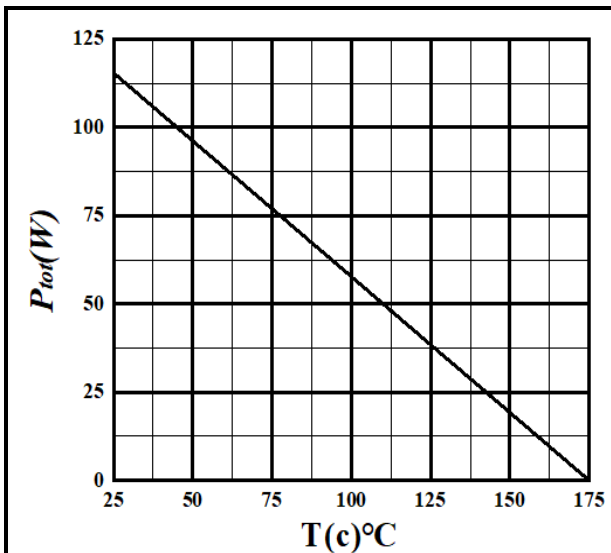


Figure 5. Power Derating

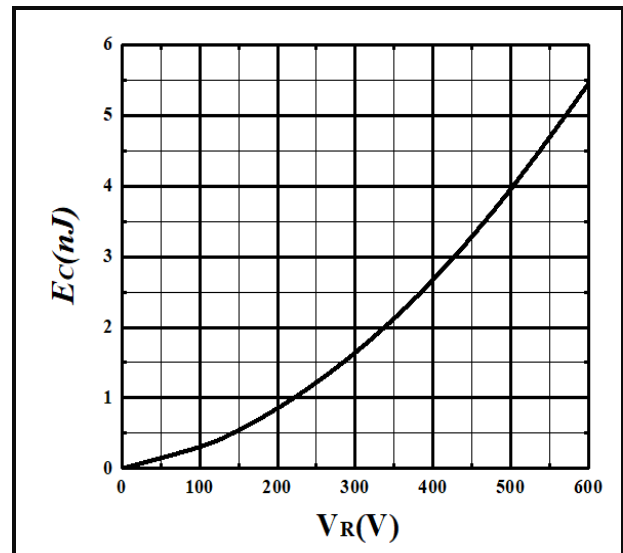


Figure 6. Capacitance Stored Energy

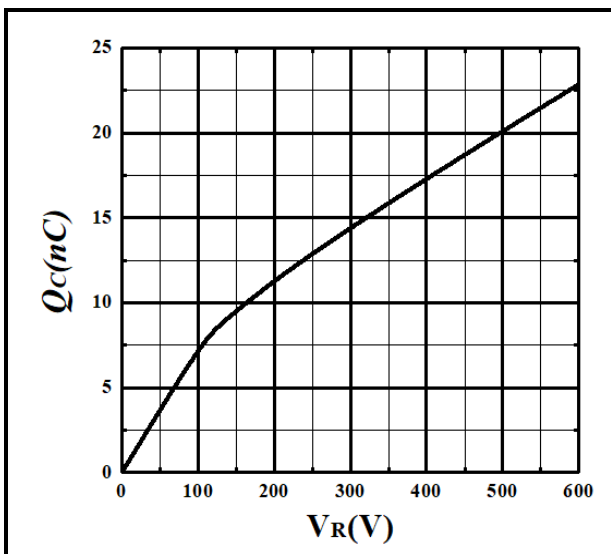
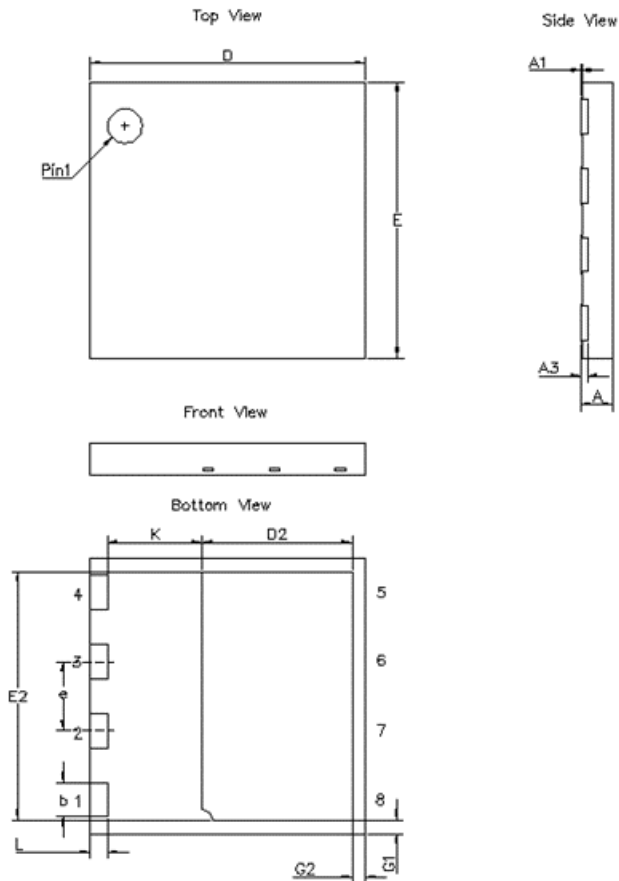


Figure 7. Total Capacitance Charge vs. Reverse Voltage

## Package



Dimension unit: [mm]			
SYMBOL	MIN	NOM	MAX
A	0.8	0.9	1
A1	0	0.02	0.05
A3	0.203REF		
b	0.9	1	1.1
D	7.9	8	8.1
E	7.9	8	8.1
D2	4.26	4.36	4.46
E2	7.1	7.2	7.3
e	1.9	2	2.1
K	2.65	2.75	2.85
L	0.4	0.5	0.6
G1	0.3	0.4	0.5
G2	0.3	0.4	0.5

## Ordering information

Part Number	SDS065J006S3-ISBRH
Package	DFN 8*8-4L
Unit Quantity	3000 EA
Packing Type	Reel
RoHS	Yes